



Corporate Presentation (ASX: WBT)

September 2017



KEY INVESTMENT HIGHLIGHTS



MASSIVE STORAGE DEMAND

Exponential increase in demand for memory storage



EXCELLENT DEVELOPMENT RESULTS

Scaled devices with a memory array significantly faster than Flash memory imminent



KEY DEVELOPMENT PARTNERSHIP

CEA-Leti, world-class research institution



MARKET DRIVERS

Content explosion and Artificial Intelligence (AI) are creating new opportunities for memory technologies (e.g. ReRAM)



ON TRACK

On target for a working 40nm cell by year end of 2017



ADDRESSABLE MARKET

> USD\$40B+



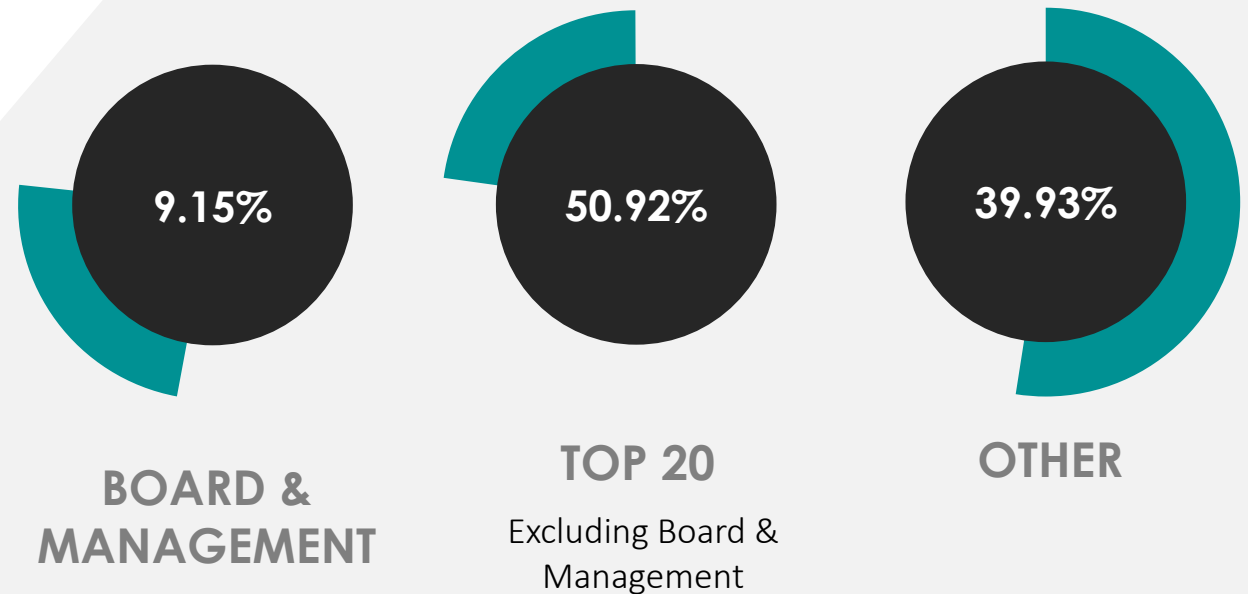
SHARE INFORMATION

CAPITAL STRUCTURE

- 01 ASX Code: WBT
- 02 Share price*: 1.8 cents
- 03 Shares on issue: 1176m
- 04 Options: 80.3m
- 05 Market cap*: \$10.8m
- 06 Cash (30 Jun 17): \$1.7m

*As of 08 Sep 2017

SHAREHOLDING BREAKDOWN





Weebit Nano AT A GLANCE



Listed on the ASX in August 2016



Targeting the storage market which is estimated at > USD\$40B



R&D and HQ in Israel, R&D partnership with CEA-Leti, France

Business & Tech partners – CEA-Leti France & Rice University, USA

Developing next-gen solution based on Silicon Oxide (SiOx) ReRAM




Patents Registered in the USA



LEADERSHIP TEAM

INVENTOR



Prof. James Tour

Scientist of the Year 2013
R&D magazine

Inducted to the National
Academy of inventors

Feynman prize in
Nano science

CHAIRMAN



David Perlmutter

Ex-Intel EVP
IEEE Fellow

Has led intel into
the Data Center

Brought to Market:
Centrino™ mobile
technology

CEO*



Yossi Keret

Extensive management
and financial experience

Financially led a variety of
international companies

Experience in equity raisings
for public companies

VP R&D



Amir Regev

Two decades in
Semiconductors engineering

45nm NOR Flash Technology
Development at Micron

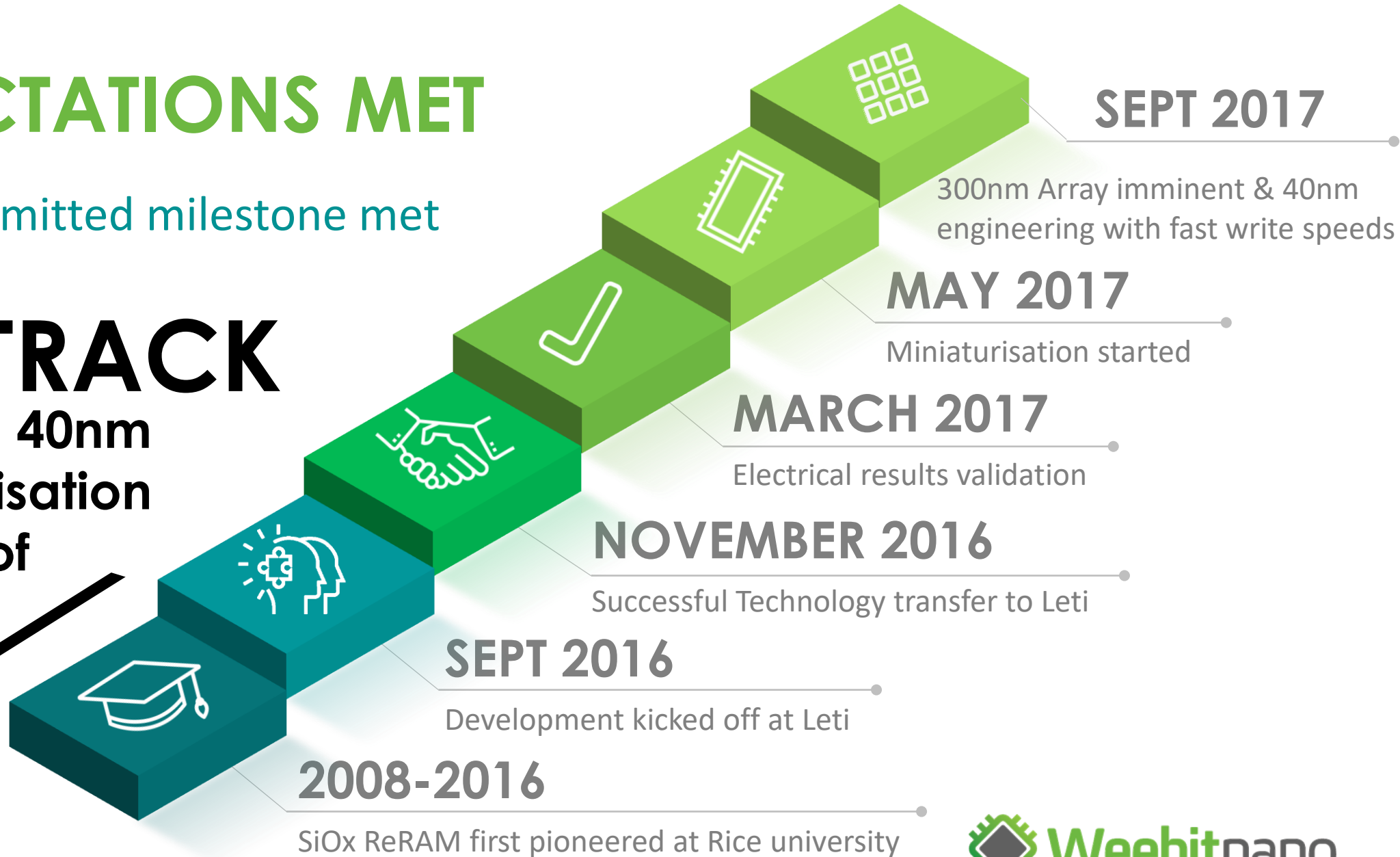
Was part of Automotive
division at Intel

*Outgoing, to be replaced by new CEO effective October 2017

EXPECTATIONS MET

Every committed milestone met

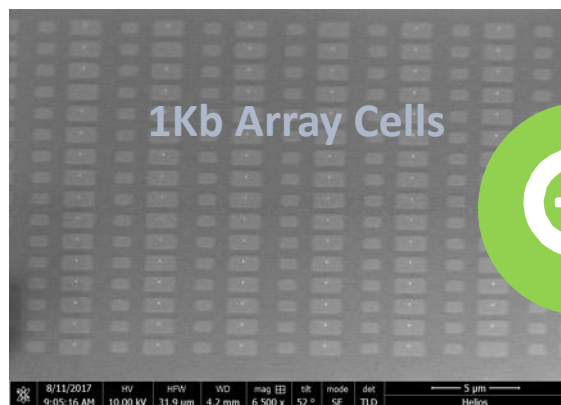
ON TRACK
to reach 40nm
miniaturisation
by end of
2017



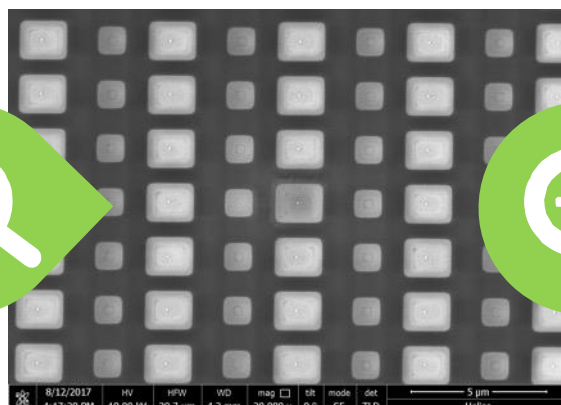
SEEING IS BELIEVING



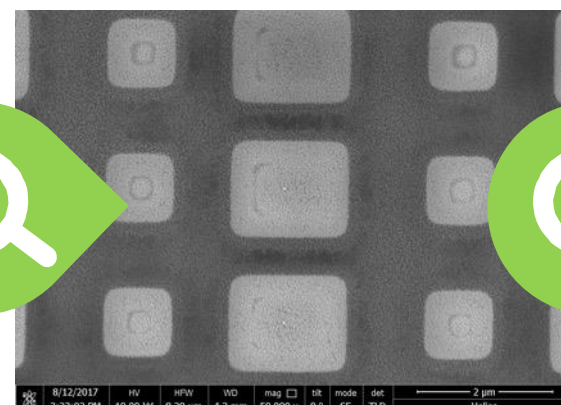
Magnified images of our ReRAM semiconductor chip



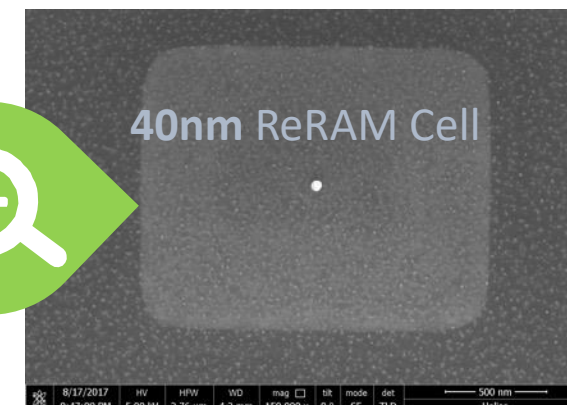
6500x
MAGNIFICATION



20,000x
MAGNIFICATION

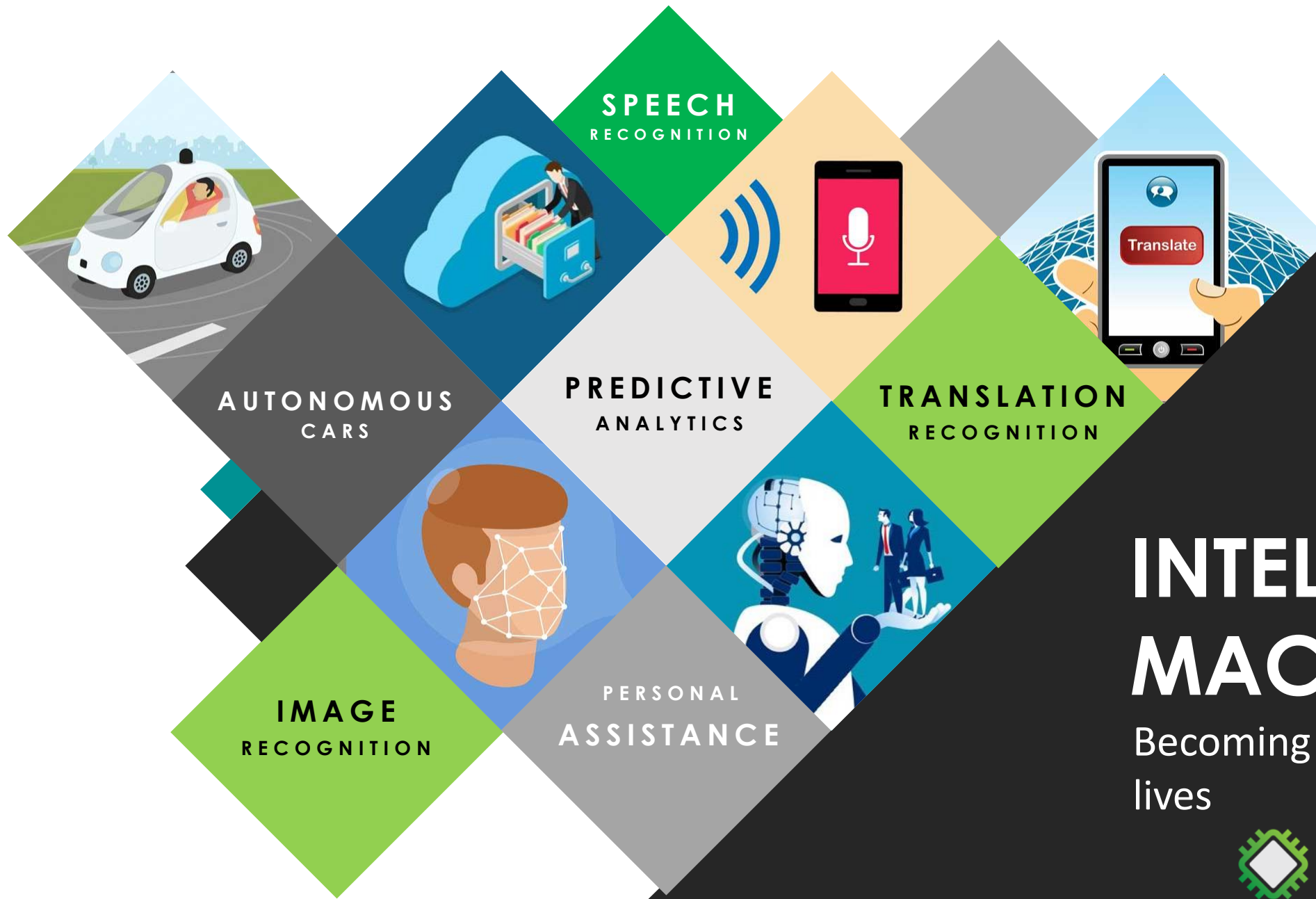


50,000x
MAGNIFICATION



200,000x
MAGNIFICATION





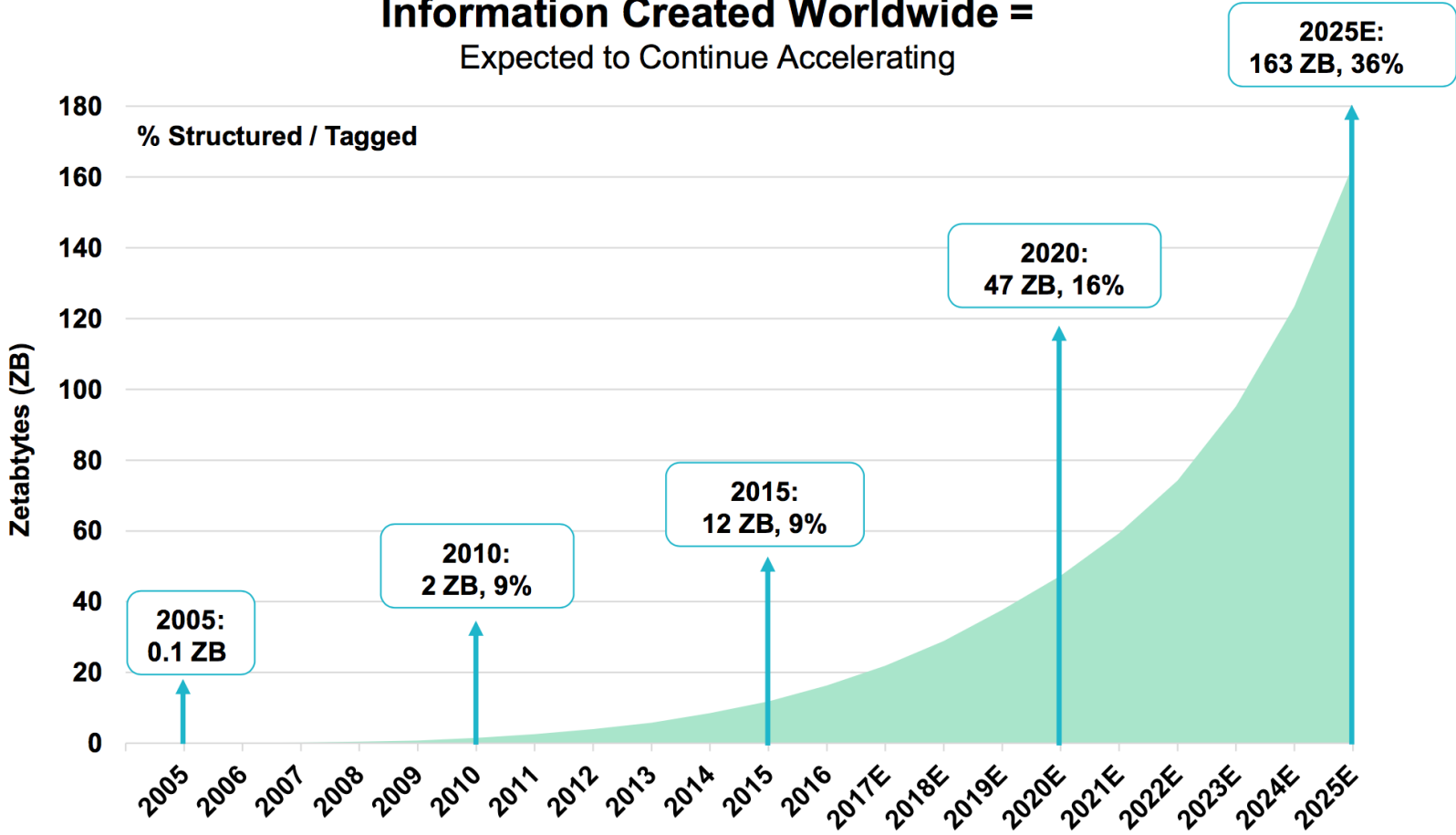
INTELLIGENT MACHINES

Becoming part of our everyday lives



DATA EXPLOSION IS COMING

Information Created Worldwide =
Expected to Continue Accelerating



Source: IDC DataAge 2025 Study, sponsored by Seagate (3/17)
Note: 1 petabyte = 1MM gigabytes, 1 zeta byte = 1MM petabytes



INDUSTRY ENDORSEMENT

NEW DATA ECONOMY

Marc Durcan

Micron CEO Micron Feb 2017

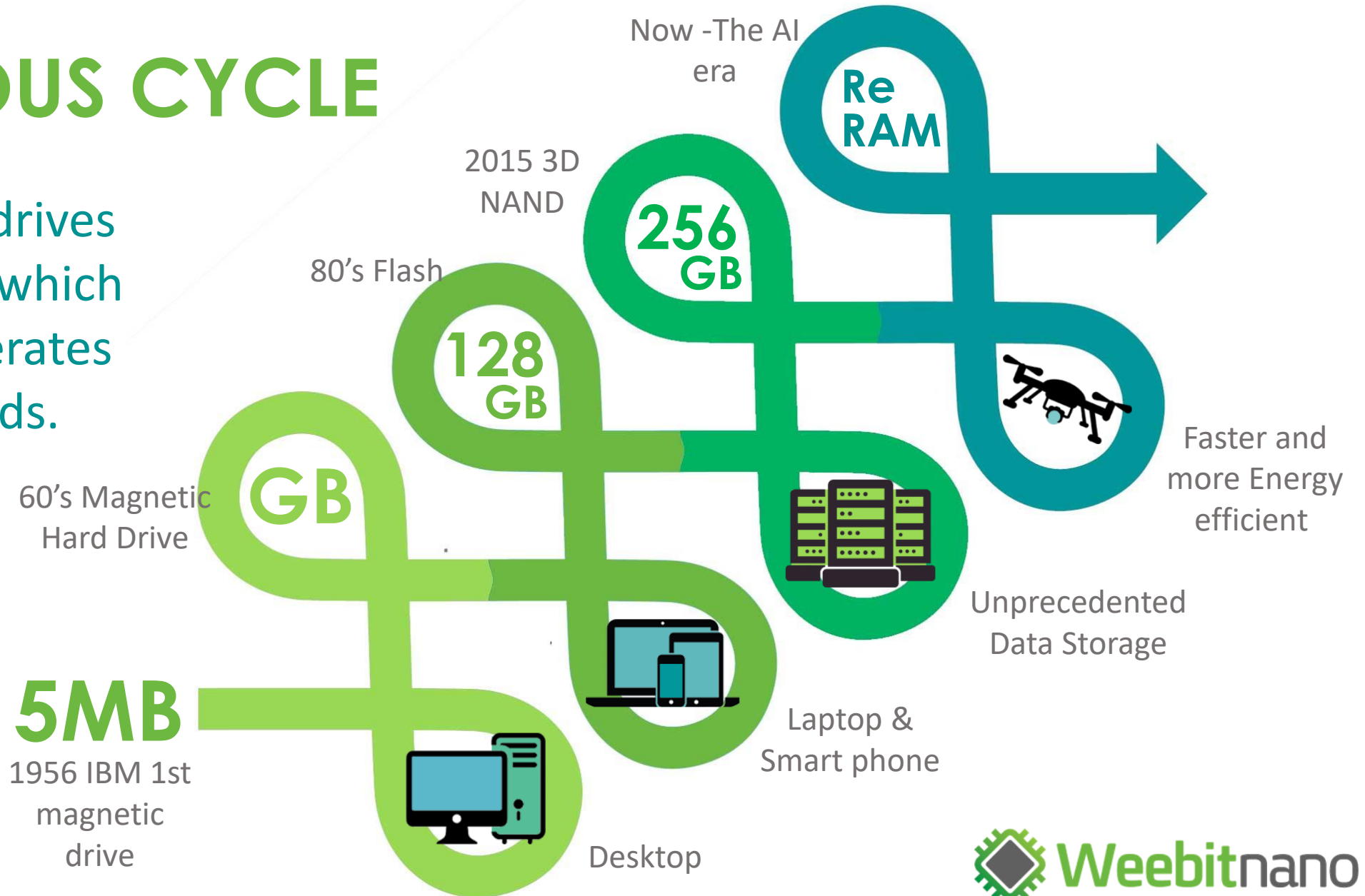


“We live in a *new data economy* that will generate huge amounts of data. Autonomous vehicles and the network that connects them will generate lots of data. The *Internet of Things* will also be a big source of data. *Cognitive computing* and *artificial intelligence* will be used to analyze much of this data”



VIRTUOUS CYCLE

Innovation drives technology which in turn generates new demands.

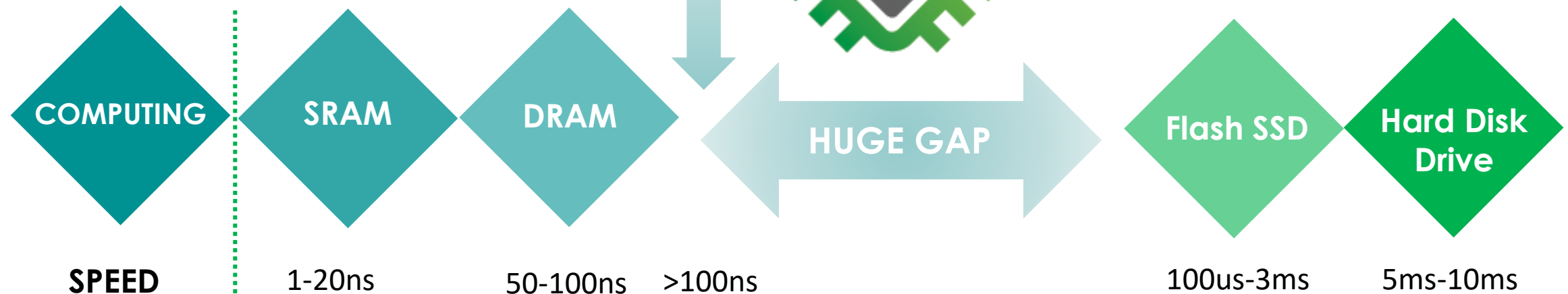


A BETTER FIT WITH EMERGING COMPUTER ARCHITECTURES

Storage Class Memory (SCM) - Closes the Gap between Memory & Computing

**LOCAL,
LOW ENERGY & FAST**
Volatile memory

**REMOTE,
HIGH ENERGY & SLOW**
Non-Volatile Storage



SPEED

ns 1 billionths of a second
us 1 millionths of a second
ms 1 thousandths of a second

Confidential





WEEBIT ReRAM TECHNOLOGY

Designed for next generation technology



ENERGY EFFICIENCY

Ultra Low Power



SPEED – READ AND WRITE

Significantly faster than Flash



INTEGRATION

Bringing the memory closer to the processor



LOW COST / NO SPECIAL MANUFACTURING TECHNOLOGY & NO RETOOLING

Manufacturability - minimum added process steps and cost

PROMISING TECHNOLOGY

Ultra-fast write speed performance coupled with low energy requirements

FAST

Very fast
write speeds

Significantly faster
than flash memory



ENERGY EFFICIENT

Standard components
voltage levels

Very low voltage
levels



SCALABLE

40nm array engineering

Ongoing integration,
similar density to Flash
memory



BEST MANUFACTURABILITY = SHORTEST TIME TO MARKET

SILICON OXIDE

Weebit NANO NEXT-GEN MEMORY SOLUTION

- ✓ **Fab Friendly** – 50 year process & manufacturing experience
- ✓ **Compatibility** – well integrated with existing proven processes

SILICON OXIDE

MANUFACTURABLE ANYWHERE

- ✓ **Any Fab** – no need for specialised foundry
- ✓ **Any Tool** – no need for special tool
- ✓ **Any process** – no need for special process

H																			He
Li	Be											B	C	O		F	Ne		
Na	Mg											Al	Si	P	S	Cl	Ar		
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr		
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe		
Cs	Ba	Lu	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn		
Fr	Ra	Lr	Rf	Db	Sg	Bh	Hs	Mt	Ds	Rg	Cn								
			Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu			
			Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr			

■ ReRAM Not Used in Semiconductor Fabs ■ Used in Semiconductor Fabs

Silicon Oxide – Shortest time to market



COMPETITIVE ADVANTAGE

Faster and Cheaper to Manufacture



	Weebitnano	4DS	Crossbar	adesto
Materials	Silicon Oxide	Pr, Ca, Mn*	Silver	Tellurium
Manufacturability	Production ready materials	Difficult to run in a production Fab	Difficult to run in a production Fab	Difficult to run in a production Fab
Speed	Fast RD & WT	Fast RD no data on WT	Fast RD & WT	Fast RD & WT
Conclusions	Most cost effective process	High Cost of manufacturing	High Cost of manufacturing	High Cost of manufacturing

Based on public information



SHORTEST TIME TO PROTOTYPE



Memory Capacity

Kb Array this year
Mb Array next year

No Array was published

8Mb Array

512Kb

Dimension

300nm
40nm

40nm

40nm

130nm

Development time

<2 years*

7 years

7 years

>10 years

Based on public information

**Time to commercially viable product*



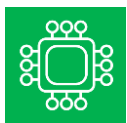
ALLIANCE WITH CEA - LETI

Partnering for highly manufacturable ReRAM



FROM PROTOTYPES TO PRODUCTION

Proven international track record in moving from R&D to production



MEMORY EXPERTISE

Over 10 years of experience in memory technology development



NANOTECHNOLOGY SPECIALIST

State of the art industrial tools



MANUFACTURING ALLIANCES

Over 330 industrial partners



INNOVATION HUB

60+ start-ups in semiconductor, architectures or software



COLLABORATION

Working on 40nm SiOx development since September 2016



CUSTOMERS

Intel, ST Microelectronics, Globalfoundries



TECHNOLOGY ROADMAP & KEY BUSINESS MILESTONES

TECHNOLOGY DEVELOPMENT

BUSINESS DEVELOPMENT

PARTNERSHIP WITH INDUSTRY LEADERS

STRATEGY

MINIATURIZATION

Technology transfer to Leti

Technology Demonstration

Initial discussion with Industry leaders (manufacturing, components, systems, Industry leaders)

Integration and characterisation 40nm 1Mb array

Scaling towards 40nm

300nm
Working cells targeted
Significant Milestone Towards 40nm

300nm Kb Array

40nm
Working cells

40nm
Kb Array

40nm
Mb Array

2017

2018



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DISCLAIMER

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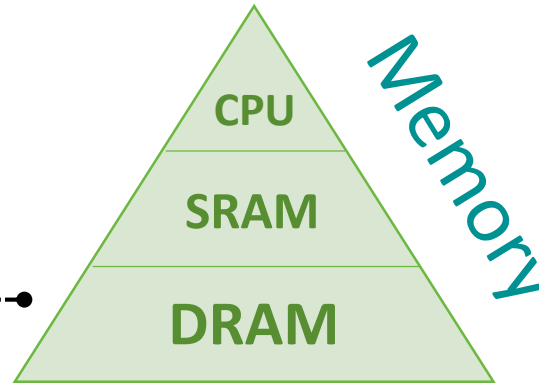


THANK YOU

STORAGE CLASS MEMORY – A PRIMER

Bridging the gap between memory & storage

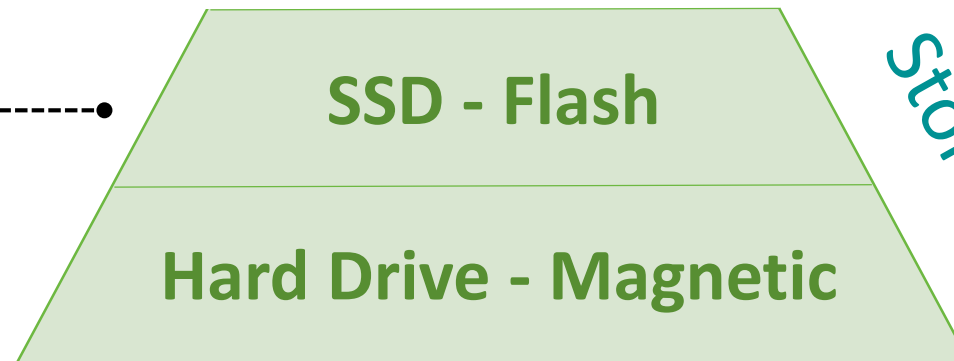
Very Fast, close to the CPU but very Expensive



VOLATILE MEMORY
loses data when power is off

STORAGE CLASS MEMORY

Slow, cheap but far from the CPU



NON-VOLATILE MEMORY
Data is stored even when power is off

